

What is claimed is:

1. A laser diode comprising:

a first clad layer of a first conductivity type formed on a substrate;

5 an active layer formed at an upper layer of said first clad layer;

a second clad layer of a second conductivity type formed at an upper layer of said active layer;

10 10 type formed at an upper layer of said second clad layer in a current injection stripe region;

a contact layer formed at an upper layer of said third clad layer; and

15 15 second clad layer in regions other than said current injection stripe region and to connect said contact layer;

whereby when a first current is injected from said electrode via said contact layer by applying a predetermined voltage to said electrode and laser light is emitted from a laser light oscillation region near said active layer, a second current which is smaller than said first current is injected in regions other than said current injection stripe region from said electrode via 20 20 said second clad layer and currents at ends of said laser

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light oscillation region are controlled for self pulsation.

2. A laser diode as set forth in claim 1, wherein saturable absorption regions are formed at said ends of
5 the laser light oscillation region for self pulsation.

3. A laser diode as set forth in claim 1, wherein said second clad layer comprises a AlGaInP-based material.

4. A laser diode as set forth in claim 1, wherein
10 a material of said electrode at a portion contacting said second clad layer comprises titanium.

5. A laser diode as set forth in claim 4, wherein said electrode comprises stacked layers of titanium, platinum, and gold and formed so as to contact said
15 second clad layer and contact layer from the titanium side.

6. A laser diode as set forth in claim 1,
comprising an etching stop layer between said second clad
layer and said third clad layer.

20 7. A laser diode as set forth in claim 1, wherein a degree of self pulsation can be adjusted by a thickness of said third clad layer and a width of said current injection stripe region.

25 8. A laser diode as set forth in claim 1, wherein a thickness of said third clad layer is in a range of 0.1

to 0.7 μm .

9. A laser diode as set forth in claim 1, wherein
a width of said current injection stripe region is in a
range of 1.5 to 5 μm .

5 10. A semiconductor light emitting device
comprising a plurality of laser diode elements, wherein
at least one of said laser diode elements comprises:

a first clad layer of a first conductivity type
formed on a substrate;

10 an active layer formed at an upper layer of
said first clad layer;

a second clad layer of a second conductivity
type formed at an upper layer of said active layer;

15 a third clad layer of the second conductivity
type formed at an upper layer of said second clad layer
in a current injection stripe region;

a contact layer formed at an upper layer of
said third clad layer; and

20 an electrode formed so as to connect said
second clad layer in regions other than said current
injection stripe region and to connect said contact
layer; and

25 whereby said at least one of said laser diode
elements is a laser diode wherein, when a first current
is injected from said electrode via said contact layer by

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applying a predetermined voltage to said electrode and a laser light is emitted from a laser light oscillation region near said active layer, a second current which is smaller than said first current is injected in regions 5 other than said current injection stripe region from said electrode via said second clad layer and currents at ends of said laser light oscillation region are controlled for self pulsation.

11. A semiconductor light emitting device as set forth in claim 10, wherein said plurality of laser diode elements are formed on said same substrate.

12. A method of producing a laser diode, including the steps of:

forming a first clad layer of a first conductivity type on a substrate;
15 forming an active layer at an upper layer of said first clad layer;
forming a second clad layer of a second conductivity type at an upper layer of said active layer;
20 forming a third clad layer of the second conductivity type at an upper layer of said second clad layer;
forming a contact layer at an upper layer of said third clad layer;
25 forming a mask layer for protecting a current

injection stripe region;

removing said third clad layer and said contact layer while leaving the current injection stripe region by using said mask layer as a mask; and

5 forming an electrode so as to connect to said second clad layer in regions other than said current injection stripe region and to connect said contact layer.

13. A method of producing a laser diode as set

10 forth in claim 12, further including the step of forming an etching stop layer at an upper layer of said second clad layer between the step of forming said second clad layer and the step of forming said third clad layer; wherein:

15 said third clad layer is formed at an upper layer of said etching stop layer in the step of forming said third clad layer; and

said third clad layer and said contact layer are removed by using said etching stop layer as an etching stop and furthermore etching conditions are changed for removing said etching stop layer in the step of removing said third clad layer and said contact layer.

14. A method of producing a laser diode as set forth in claim 12, wherein titanium is used as a material 20 of said electrode of a portion contacting said second

clad layer in the step of forming said electrode.

15. A method of producing a laser diode as set forth in claim 14, wherein stacked layers of titanium, platinum, and gold are formed as the above electrode so 5 as to contact said second clad layer and contact layer from its titanium side in the step of forming said electrode.

16. A method of producing a laser diode as set forth in claim 12, wherein a thickness of said third clad 10 layer is formed to be in a range of 0.1 to 0.7 μm .

17. A method of producing a laser diode as set forth in claim 12, wherein a width of said current injection stripe region is formed to be in a range of 1.5 to 5 μm .

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